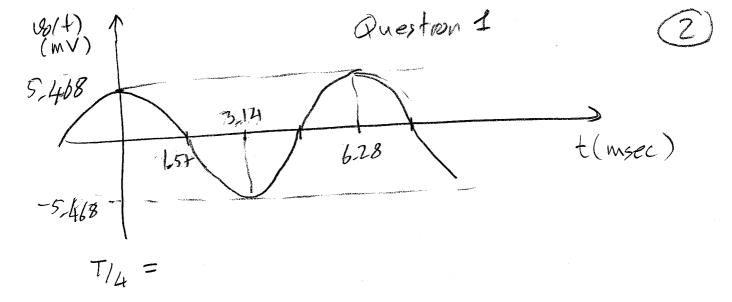


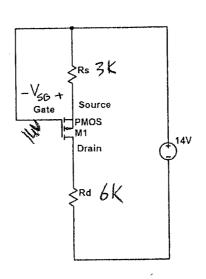
1. (25 points) At the circuit given above, the diode  $V\gamma = 0.6 V$ olts. The value of the resistor  $R_2$  is  $15\Omega$ .  $V_1 = 10 V$ olts,  $R_1 = 2k\Omega$ ,  $C_1$  and  $C_2$  are very large.  $V_2(t)$  is equal to 0.02 cos(1000t) Volts. The diode is at room temperature and the ideality factor n=1. Answer the following:

- a. (6 points) Find the DC current, IDQ, through the diode,
- b. (6 points) Draw the AC equivalent circuit,
- c. (7 points) Calculate and plot  $v_0(t)$ , carefully label the time axis and zero-crossing points.
- d. (6 points) Do we expect to see an undistorted or distorted sinusoidal wave over the diode? Please state the reason behind your answer.



(d) We expect to see on undistorted waveform because  $|v_0(t)|_{peak}$   $|V_T = 26.6 \text{mV}$ 





- 2. (20 points) At the depletion-mode p-channel MOSFET circuit given above,  $V_{TP}$  = 3 Volts and  $K_P = 5 \times 10^{-3} \text{A/V}^2$ .  $R_d = 6 \text{k}\Omega$  and  $R_S = 3 \text{k}\Omega$ 
  - a. (15 points) Find the bias of the transistor,
  - b. (5 points) Verify the solution.

Solutions: (a)

(a) assuming saturation and witing the gate-source loop = 0 = Ep Rs + Vs6 = RsKn (Vs6 + (VTP)) + Vs6 3×10 5×10 [ Vs6 +2 Vs6 × 3 + 9] + Vs6 = 0 15 Vs 2 + 90 Vs 6 + 135 + Vs 6 = 0 =) 15 1/2 + 91 Vs6 + 135 = 0  $V_{SG_{1,2}} = \frac{-b \pm \sqrt{b^2 - 4ac'}}{30} = \frac{-91 \pm \sqrt{91^2 - 4 \times 15 \times 135'}}{30}$  $= \frac{-91 \pm \sqrt{181}}{30} = -3.033 \pm 0.448 = -2.585, -3.482$ Means cut

> VSG = -2,58488V

[ID = Kn(VSG+32-5x103(-2.58488+3)] = 8-6162×10A Vs6 = -In Rs = -8.6162×104×3×10 = -2.58488 V /

 $\frac{V_{50} = V_{0c} - (R_0 + R_5) I_D = 14 - 8 \times 10^3 \times 8.6112 \times 10^4}{= 14 - 6.89 = 7.107 V > V_{56} + V_{7P} = -2.58488 + 3 = 0.415 V}$  = 0.415 V

b-) Verifying  $V_{5G} = -I_{D}R_{5} = -5 \times 10^{3} \left[ -2.58488 + 3 \right] \times 3 \times 10^{3}$   $= -2.58488 \vee \sqrt{}$